2.5V Drive Nch MOS FET RTF015N03

Structure

Silicon N-channel MOS FET

● Features

- 1) Low On-resistance.
- 2) Space saving, small surface mount package (TUMT3).
- 3) Low voltage drive (2.5V drive).

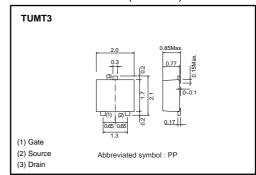
Applications

Switching

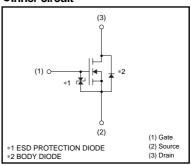
Packaging specifications

	Package	Taping	
Type	Code	TL	
	Basic ordering unit (pieces)	3000	
RTF015N03		0	

●External dimensions (Unit : mm)



•Inner circuit



●Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		VDSS	30	V
Gate-source voltage		Vgss	12	V
Drain current	Continuous	lσ	±1.5	Α
	Pulsed	IDP *1	±6.0	Α
Source current	Continuous	Is	0.6	Α
(Body diode)	Pulsed	Isp *1	6.0	Α
Total power dissipation		Pp *2	0.8	W
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

^{*1} Pw≤10μs, Duty cycle≤1% *2 Mounted on a ceramic board

●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a)*	156	°C/W

^{*} Mounted on a ceramic board

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	1	_	10	μΑ	Vgs=12V, Vps=0V
Drain-source breakdown voltage	$V_{(BR)\;DSS}$	30	_	_	V	I _D = 1mA, V _{GS} =0V
Zero gate voltage drain current	IDSS	-	_	1	μΑ	V _{DS} = 30V, V _{GS} =0V
Gate threshold voltage	V _{GS (th)}	0.5	_	1.5	V	V _{DS} = 10V, I _D = 1mA
		_	170	240	mΩ	I _D = 1.5A, V _{GS} = 4.5V
Static drain-source on-state resistance	R _{DS (on)} *	-	180	250	mΩ	I _D = 1.5A, V _{GS} = 4V
resistance		-	240	340	mΩ	I _D = 1.5A, V _{GS} = 2.5V
Forward transfer admittance	Y _{fs} *	1.5	_	_	S	V _{DS} = 10V, I _D = 1.5A
Input capacitance	Ciss	-	80	_	pF	V _{DS} = 10V
Output capacitance	Coss	_	14	_	pF	V _G s=0V
Reverse transfer capacitance	Crss	_	12	_	pF	f=1MHz
Turn-on delay time	t _{d (on)} *	_	7	_	ns	V _{DD} ≒ 15V
Rise time	tr *	-	9	_	ns	ID= 0.75A
Turn-off delay time	t _{d (off)} *	_	15	_	ns	V _{GS} = 4.5V R _L =20Ω
Fall time	t _f *	-	6	_	ns	R _G =10Ω
Total gate charge	Qg *	_	1.6	2.2	nC	V _{DD} =15V V _{GS} =4.5V
Gate-source charge	Q _{gs} *	-	0.5	-	nC	I _D = 1.5A
Gate-drain charge	Q _{gd} *	_	0.3	_	nC	RL= 10Ω RG= 10Ω

*Pulsed

●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsp	-	_	1.2	V	I _S = 0.6A, V _{GS} =0V

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